

<b>SANYO</b>	No. 1721A	<b>2SB1126/2SD1626</b>
		PNP/NPN Epitaxial Planar Silicon Transistors For Various Drivers

**Applications**

- . Relay drivers, hammer drivers, lamp drivers, motor drivers.

**Features**

- . High DC current gain (4000 or greater).
- . Large current capacity.
- . Very small size making it easy to provide high-density, small-sized hybrid IC's.

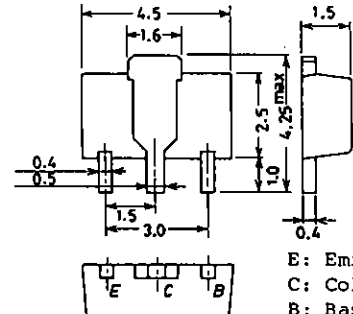
( ): 2SB1126

Absolute Maximum Ratings at Ta=25°C			unit
Collector to Base Voltage	V <sub>CB0</sub>	(-)80	V
Collector to Emitter Voltage	V <sub>CEO</sub>	(-)50	V
Emitter to Base Voltage	V <sub>EBO</sub>	(-)10	V
Collector Current	I <sub>C</sub>	(-)1.5	A
Collector Current(Pulse)	I <sub>CP</sub>	(-)3	A
Collector Dissipation	P <sub>C</sub>	500	mW
	Mounted on ceramic board (250mm <sup>2</sup> x 0.8mm)	1.5	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

Electrical Characteristics at Ta=25°C			min	typ	max	unit
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =(-)40V, I <sub>E</sub> =0			(-)100	nA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =(-)8V, I <sub>C</sub> =0			(-)100	nA
DC Current Gain	h <sub>FE1</sub>	V <sub>CE</sub> =(-)2V, I <sub>C</sub> =(-)500mA	4000			
	h <sub>FE2</sub>	V <sub>CE</sub> =(-)2V, I <sub>C</sub> =(-)10mA	3000			
Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> =(-)10V, I <sub>C</sub> =(-)50mA		120		MHz
C-E Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =(-)500mA, I <sub>B</sub> =(-)0.5mA	(-)0.9	(-)1.5		V
B-E Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =(-)500mA, I <sub>B</sub> =(-)0.5mA	(-)1.5	(-)2.0		V
C-B Breakdown Voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =(-)10μA, I <sub>E</sub> =0	(-)80			V
C-E Breakdown Voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =(-)1mA, R <sub>BE</sub> =∞	(-)50			V
E-B Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =(-)10μA, I <sub>C</sub> =0	(-)10			V

Marking 2SB1126:BI  
2SD1626:DI

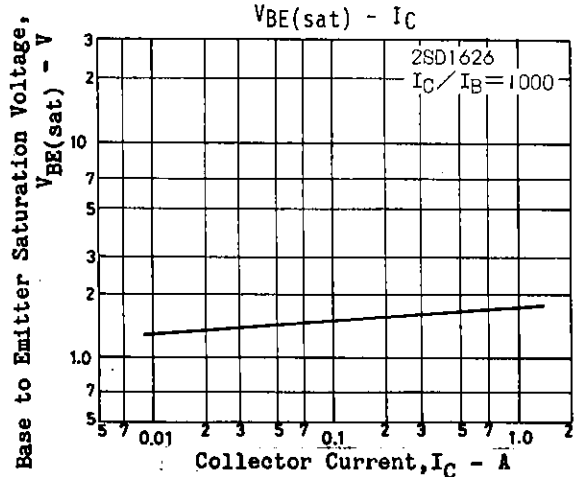
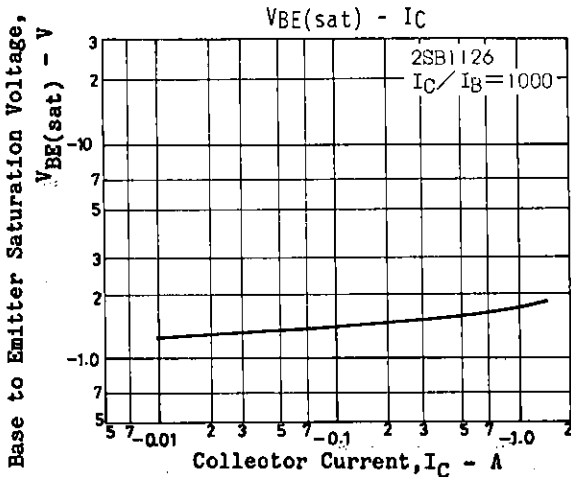
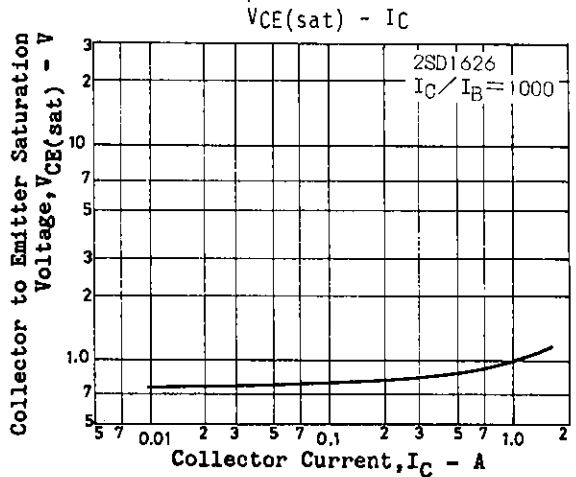
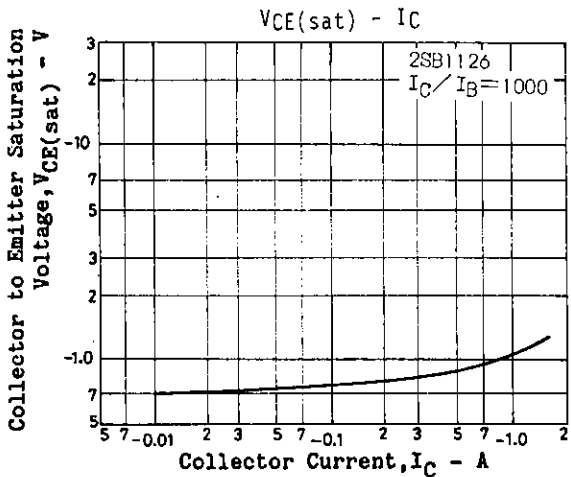
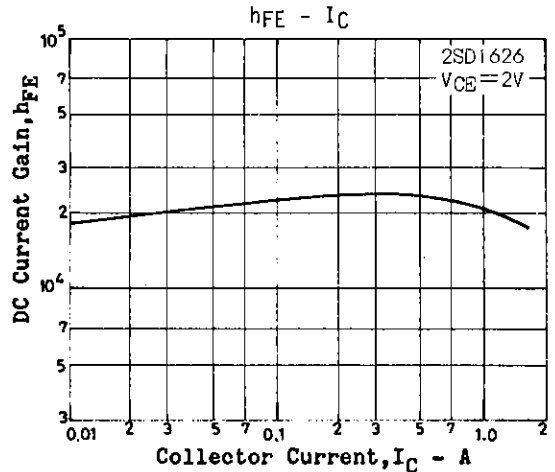
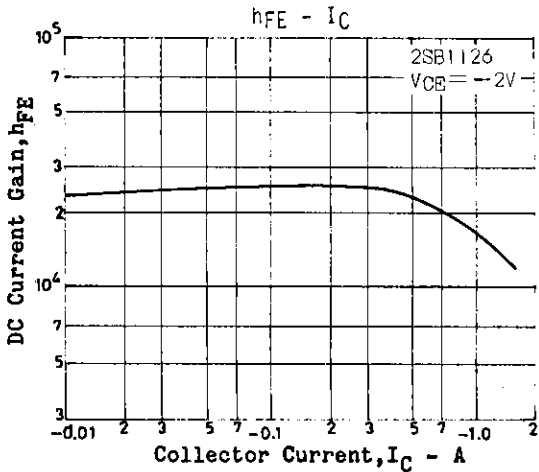
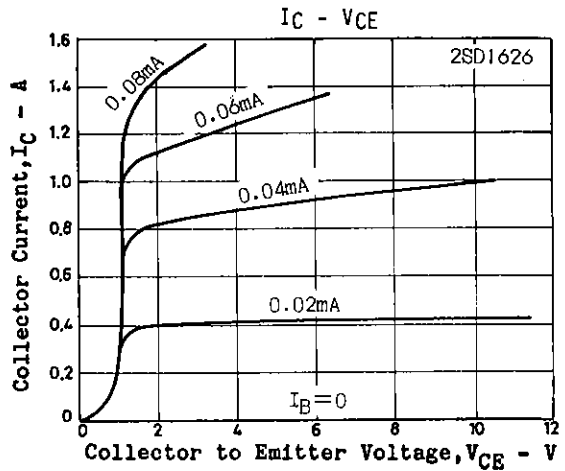
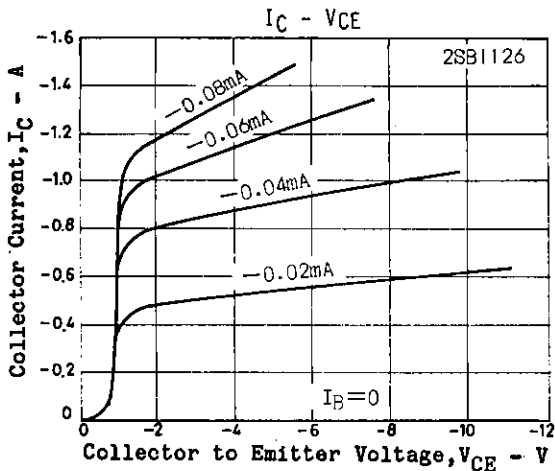
**Package Dimensions 2038**  
(unit:mm)

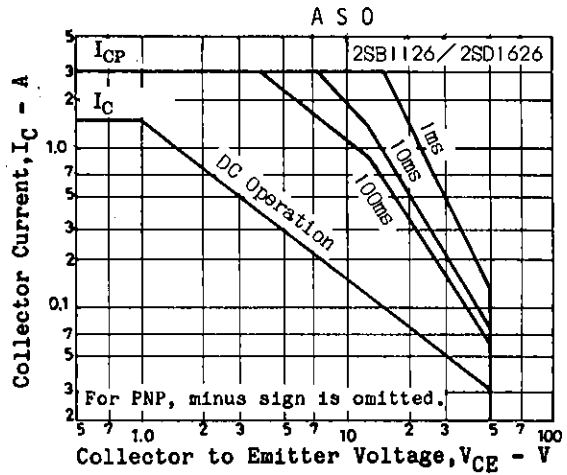
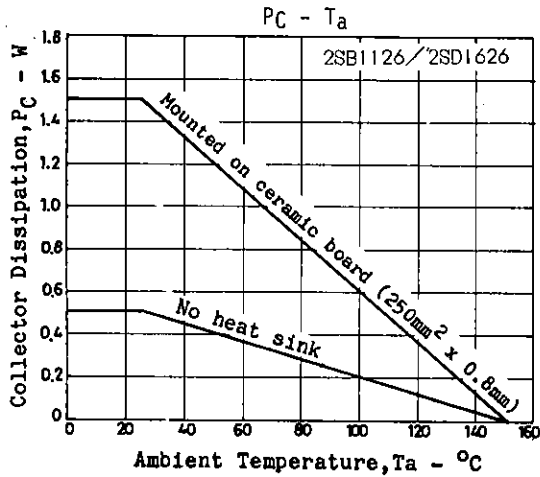


E: Emitter  
C: Collector  
B: Base

SANYO: PCP  
(Bottom View)

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